

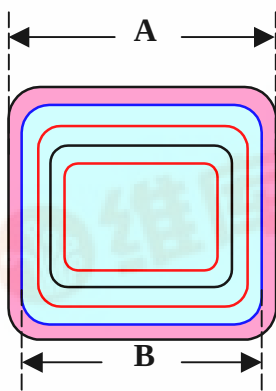


CMS-S035-040

SCHOTTKY BARRIER DIODE

Features :

- * Extremely low forward volts
- * Guard ring protection
- * Low reverse leakage current



Chip size(A): 0.889 * 0.889 mm²

Bond Pad size(B) : 0.762 * 0.762 mm²

Thickness : 300μm ± 20μm

Metalization : Anode Ti/Ni/Ag

Metalization : Cathode Ti/Ni/Ag

Electrical Characteristics	Sym.	Spec. Limit	Unit
Maximum Instantaneous Forward Volt at IF : 1.0Amp. 25°C	VF max	0.50	Volt
Minimum Instantaneous Reverse Voltage at IR : 200 uA 25°C	VR min.	43	Volt.
Minimum Non-repetitive Peak Surge current at 25°C	IFSM	30	Amp
Storage Temperature	TSTG	-65 to +125	°C

HsinChu Headquarter

5F, No. 11, Park Avenue II,
Science-Based Industrial Park,
HsinChu City, Taiwan
TEL: +886-3-567 9979
FAX: +886-3-567 9909

Sales & Marketing

11F, No. 306-3, SEC. 1, Ta Tung Road,
Hsichih, Taipei Hsien 221, Taiwan
TEL: +886-2-8692 1591
FAX: +886-2-8692 1596

